Single 2-Input AND Gate

The NL17SH08 is an advanced high speed CMOS 2-input AND gate fabricated with silicon gate CMOS technology.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output.

The NL17SH08 input structure provides protection when voltages up to 7.0 V are applied, regardless of the supply voltage. This allows the NL17SH08 to be used to interface 5.0 V circuits to 3.0 V circuits.

Features

- High Speed: $t_{PD} = 3.5 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1.0 \mu A$ (Max) at $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- These are Pb-Free Devices

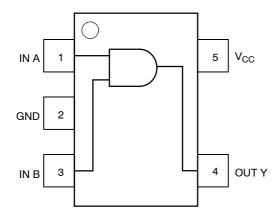


Figure 1. Pinout (Top View)



Figure 2. Logic Symbol



ON Semiconductor®

http://onsemi.com

MARKING DIAGRAM



SOT-953 CASE 527AE



E = Specific Device Code

M = Month Code

PIN ASSIGNMENT					
1 IN A					
2	GND				
3	IN B				
4	OUT \overline{Y}				
5	V _{CC}				

FUNCTION TABLE

Inp	uts	Output
Α	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	н

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

NL17SH08

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	DC Input Voltage	-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	-0.5 to V _{CC} +0.5	V
I _{IK}	DC Input Diode Current	-20	mA
I _{OK}	DC Output Diode Current	±20	mA
I _{OUT}	DC Output Sink Current	±25	mA
I _{CC}	DC Supply Current per Supply Pin	50	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias	+150	°C
P_{D}	Power Dissipation in Still Air	50	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
I _{LATCHUP}	Latchup Performance Above V _{CC} and Below GND at 125°C (Note 1)	±100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit	
V _{CC}	DC Supply Voltage	2.0	5.5	V	
V _{IN}	DC Input Voltage			5.5	V
V _{OUT}	DC Output Voltage	0.0	V _{CC}	V	
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	ns/V

Device Junction Temperature versus Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

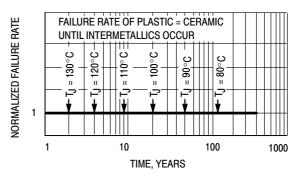


Figure 3. Failure Rate vs. Time Junction Temperature

Tested to EIA/JESD78.

NL17SH08

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	Т	A = 25°	С	T _A ≤	85°C	−55°C t	to 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	٧
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OH} = -4 \text{ mA} \\ I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	٧
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 4$ mA $I_{OL} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			1.0		10	_	40	μΑ

AC ELECTRICAL CHARACTERISTICS Input t_{r} = t_{f} = 3.0 ns

		T _A = 25°C		T _A ≤ 85°C		$-55 \le T_A \le 125$ °C					
Symbol	Parameter	Test Condition	ns	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propaga- tion Delay, Input A or B to Y		C _L = 15 pF C _L = 50 pF		4.1 5.9	8.8 12.3		10.5 14.0		12.5 16.5	ns
	Input A or B to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		3.5 4.2	5.9 7.9		7.0 9.0		9.0 11.0	
C _{IN}	Maximum Input Ca- pacitance				5.5	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 2)	11	pF

^{2.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NL17SH08

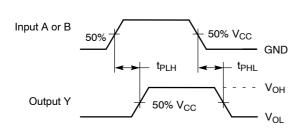
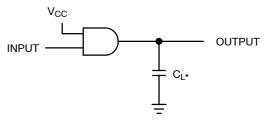


Figure 4. Switching Waveforms



*Includes all probe and jig capacitance. A 1-MHz square input wave is recommended for propagation delay tests.

Figure 5. Test Circuit

DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]
NL17SH08P5T5G	SOT-953 (Pb-Free)	8000 / Tape & Reel

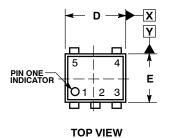
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

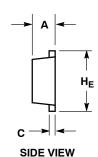


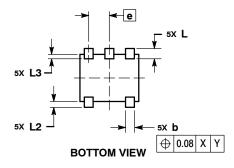
SOT-953 CASE 527AE **ISSUE E**

DATE 02 AUG 2011

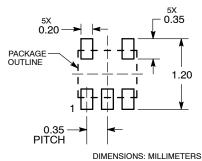








SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS						
DIM	MIN NOM MAX						
Α	0.34	0.37	0.40				
b	0.10	0.15	0.20				
С	0.07	0.12	0.17				
D	0.95	1.00	1.05				
E	0.75	0.80	0.85				
е		0.35 BS	С				
HE	0.95	1.00	1.05				
L	(0.175 REF					
L2	0.05	0.10	0.15				
L3			0.15				

GENERIC MARKING DIAGRAM*



= Specific Device Code = Month Code

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON26457D	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOT-953		PAGE 1 OF 1		

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative